## SPICE Device Model SUP85N10-10, SUB85N10-10



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# N-Channel 100 V (D-S) 175 °C MOSFET

#### **DESCRIPTION**

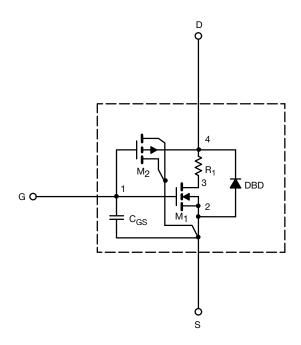
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{\rm gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

#### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Sub-circuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

#### SUBCIRCUIT MODEL SCHEMATIC



#### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1.9	-	V
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	588	-	Α
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	0.0083	0.0085	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	0.014	-	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	0.017	-	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	84	-	S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 85 A, V <sub>GS</sub> = 0 V	0.92	1	V
Dynamic <sup>b</sup>	•		•		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	6456	6550	pF
Output Capacitance	Coss		713	665	
Reverse Transfer Capacitance	C <sub>rss</sub>		238	265	
Total Gate Charge <sup>c</sup>	Qg	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 85 \text{ A}$	107	105	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		17	17	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		23	23	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 0.6 \Omega$ $I_{D} = 85 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 2.5 \Omega$ $I_{F} = 50 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$	17	12	ns
Rise Time <sup>c</sup>	t <sub>r</sub>		10	90	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		25	25	
Fall Time <sup>c</sup>	t <sub>f</sub>		22	130	
Source-Drain Reverse Recovery Time b	t <sub>rr</sub>		75	85	

#### Notes

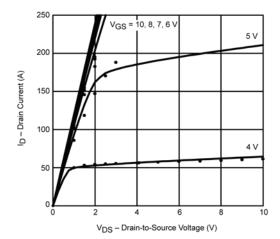
- a. Pulse test; pulse width  $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

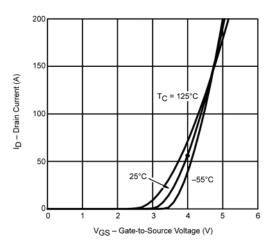


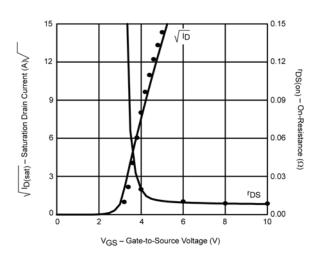
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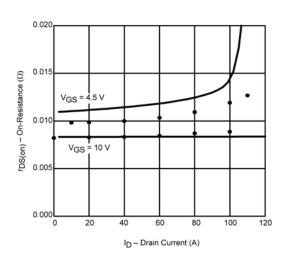
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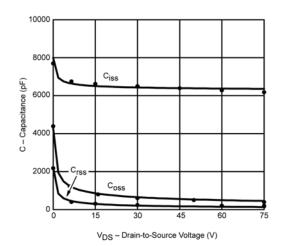
### COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)

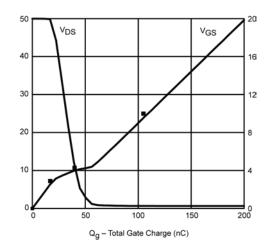












#### Note

Dots and squares represent measured data.
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